



DMP2022LSS

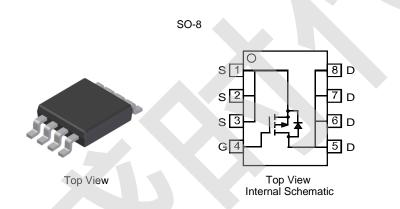
Features

- Low On-Resistance
 - $13m\Omega @ V_{GS} = -10V$.
 - $16m\Omega @ V_{GS} = -4.5V$ •
 - 22mΩ @ V_{GS} = -2.5V
 - Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- An Automotive-Compliant Part is Available Under Separate Datasheet

SINGLE P-CHANNEL ENHANCEMENT MODE MOSFET

Mechanical Data

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- **Terminals Connections: See Diagram**
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.072g (Approximate)



Ordering Information (Note 4)

Part Number	Case	Packaging
DMP2022LSS-13	SO-8	2500/Tape & Reel

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. 2. See http:// /quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green"

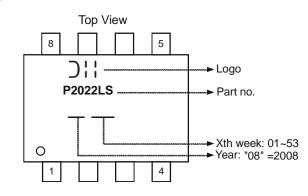
and Lead-free

Notes:

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https:// /design/support/packaging/diodes-packaging/.

Marking Information





Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Char	acteristic		Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	-20	V
Gate-Source Voltage			V _{GSS}	±12	V
Drain Current (Note 5)	Steady State	T _A = +25°C T _A = +70°C	ID	-10 -8	А
Pulsed Drain Current (Note 6)			I _{DM}	-90	А

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	PD	2.5	W
Thermal Resistance, Junction to Ambient	R _{0JA}	50	°C/W
Operating and Storage Temperature Range	T _{J,} T _{STG}	-55 to +150	°C

Notes: 5. Device mounted on 2 oz. Copper pads on FR-4 PCB.

6. Pulse width ${\leq}10\mu S,$ Duty Cycle ${\leq}1\%.$

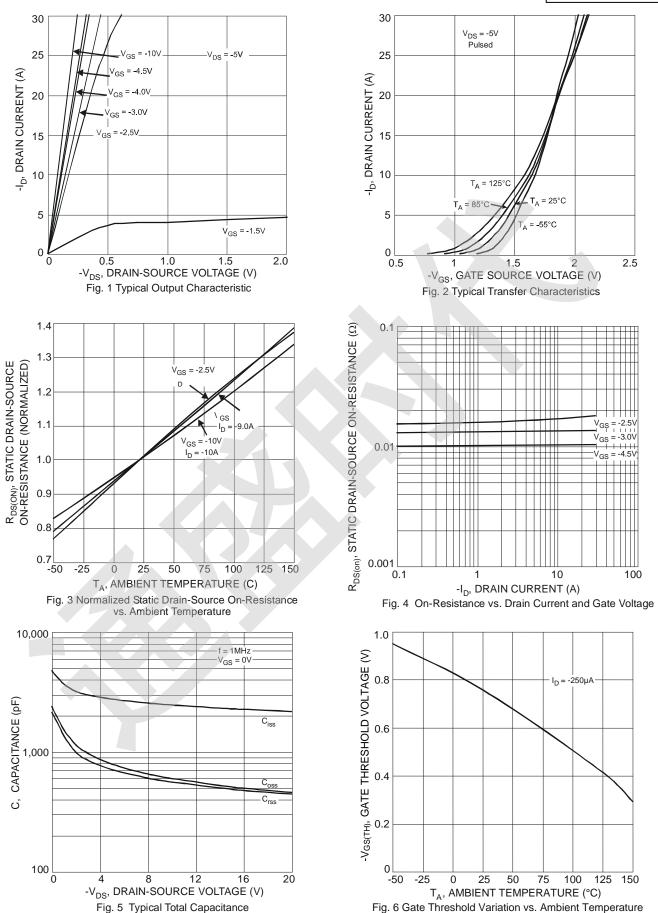
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)			<u>- 7</u>				
Drain-Source Breakdown Voltage	BV _{DSS}	-20			V	$V_{GS} = 0V, I_D = -250 \mu A$	
Zero Gate Voltage Drain Current	IDSS		_	-1	μΑ	$V_{DS} = -20V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}		-	±100	nA	$V_{GS} = \pm 12V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	VGS(TH)	-0.6	-0.77	-1.1	V	$V_{DS} = V_{GS}, I_D = -250 \mu A$	
			8	13	mΩ	$V_{GS} = -10V, I_D = -10A$	
Static Drain-Source On-Resistance	RDS(ON)		11	16		$V_{GS} = -4.5V, I_D = -9A$	
			17	22		$V_{GS} = -2.5V, I_D = -8A$	
Forward Transconductance	g fs	<u> </u>	28		S	$V_{DS} = -10V, I_D = -10A$	
Diode Forward Voltage (Note 7)	V _{SD}	-0.5	-0.68	-1.2	V	$V_{GS} = 0V, I_{S} = -3A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C _{iss}	_	2444	_	pF		
Output Capacitance	C _{oss}	_	594	_	pF	−V _{DS} = -10V, V _{GS} = 0V −f = 1.0MHz	
Reverse Transfer Capacitance	Crss	_	556	_	pF		
Gate Resistance	R _G	_	2.0	_	Ω	$V_{GS} = 0V, V_{DS} = 0V, f = 1MHz$	
SWITCHING CHARACTERISTICS (Note 8)			_	_			
Total Gate Charge	Qg	28	28.1 — 56.9 —		$V_{DS} = -10V, V_{GS} = -4.5V, I_D = -10A$		
Total Gate Charge					nC	$V_{DS} = -10V, V_{GS} = -10V, I_D = -10A$	
Gate-Source Charge	Q _{gs}	—	3.4	—	nC	$V_{DS} = -10V, V_{GS} = -10V, I_D = -10A$	
Gate-Drain Charge	Q _{gd}	_	11.9			$V_{DS} = -10V, V_{GS} = -10V, I_D = -10A$	
Turn-On Delay Time	t _{D(ON)}	_	7.5	15			
Turn-On Rise Time	t _R	_	9.9	20		$V_{DD} = -15V, I_D = -1A, V_{GS} = -10V,$	
Turn-Off Delay Time	t _{D(OFF)}		108.0	216	ns	$R_{GEN} = 6\Omega$	
Turn-Off Fall Time	t _F	_	76.5	153	1		

7. Short duration pulse test used to minimize self-heating effect. Notes: 8. Guaranteed by design. Not subject to product testing.







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 ● List:0755-83387360

 手机:13826508770(王先生)

 邮箱:3007605919@qq.com

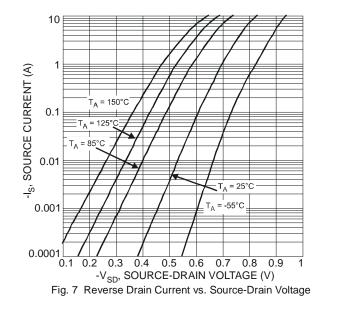
 网址:www.sztssd.com

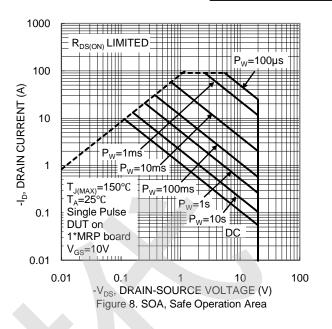
 地址:深圳市福田区中航路鼎诚国际南座18楼1814室

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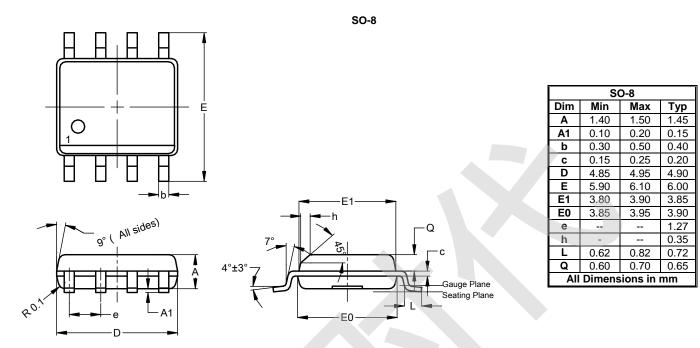






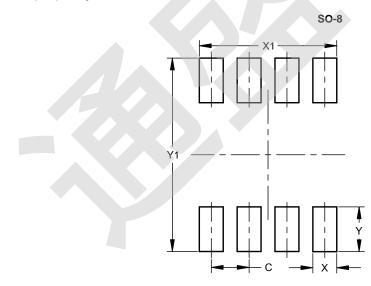
Package Outline Dimensions

Please see http:///package-outlines.html for the latest version.



Suggested Pad Layout

Please see http:///package-outlines.html for the latest version.



Dimensions	Value (in mm)
С	1.27
Х	0.802
X1	4.612
Y	1.505
Y1	6.50



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